# **BLF8G24LS-100V**; BLF8G24LS-100GV

Power LDMOS transistor Rev. 1 — 4 November 2013

**Objective data sheet** 

### 1. Product profile

### 1.1 General description

100 W LDMOS power transistor with improved video bandwidth for base station applications at frequencies from 2300 MHz to 2400 MHz.

#### Table 1. **Typical performance**

Typical RF performance at T<sub>case</sub> = 25 °C in a common source class-AB production test circuit.

Test signal	f	I <sub>Dq</sub>	$V_{\text{DS}}$	P <sub>L(AV)</sub>	Gp	$\eta_D$	ACPR <sub>5M</sub>
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	2300 to 2400	900	28	25	17	28	-32 <u>[1]</u>

[1] Test signal: 3GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF per carrier; 5 MHz carrier spacing.

### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth (110 MHz typical)
- Designed for broadband operation (2300 MHz to 2400 MHz)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

#### 1.3 Applications

RF power amplifiers for W-CDMA base stations and multi carrier applications in the 2300 MHz to 2400 MHz frequency range



### 2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
BLF8G24	LS-100V (SOT1244B)		
1	drain		
2	gate	4 1 5 $1$	6,7 → I <b>↓</b> 4,5
3	source		
4	decoupling lead	3	2     3
5	decoupling lead		aaa-003619
6	n.c.		
7	n.c.	6 2 7	
BLF8G24	LS-100GV (SOT1244C)		
1	drain		
2	gate		6 7 → 1 → 4.5
3	source	1	6,7 → 2 → 4,5
4	decoupling lead		2
5	decoupling lead		aaa-003619
6	n.c.	6 2   7 3	
7	n.c.		

[1] Connected to flange.

### 3. Ordering information

#### Table 3. Ordering information

Type number	Packag	je	
	Name	Description	Version
BLF8G24LS-100V	-	earless flanged ceramic package; 6 leads	SOT1244B
BLF8G24LS-100GV	-	earless flanged ceramic package; 6 leads	SOT1244C

### 4. Limiting values

#### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage			-	65	V
$V_{GS}$	gate-source voltage			-0.5	+13	V
T <sub>stg</sub>	storage temperature			-65	+150	°C
Tj	junction temperature		<u>[1]</u>	-	225	°C

[1] Continuous use at maximum temperature will affect reliability.

### 5. Thermal characteristics

Table 5.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	$T_{case} = 80 \ ^{\circ}C; P_{L} = 48 \ W$	0.29	K/W

### 6. Characteristics

#### Table 6. DC characteristics

 $T_i = 25 \ ^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$V_{GS} = 0 V; I_D = 1 mA$	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$V_{DS}$ = 10 V; $I_{D}$ = 153 mA	1.5	1.9	2.3	V
I <sub>DSS</sub>	drain leakage current	$V_{GS}$ = 0 V; $V_{DS}$ = 28 V	-	-	4.2	μΑ
I <sub>DSX</sub>	drain cut-off current	$\label{eq:VGS} \begin{array}{l} V_{GS} = V_{GS(th)} + 3.75 \; V; \\ V_{DS} = 10 \; V \end{array}$	-	29	-	A
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 11 \text{ V}; V_{DS} = 0 \text{ V}$	-	-	420	nA
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; I <sub>D</sub> = 153 mA	-	1.27	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 5.35 A$	-	0.1	-	Ω

#### Table 7. RF characteristics

Test signal: 2-carrier W-CDMA, 3GPP test model 1; 64 DPCH; PAR = 7.2 dB at 0.01 % probability on the CCDF;  $f_1 = 2302.5$  MHz;  $f_2 = 2307.5$  MHz;  $f_3 = 2392.5$  MHz;  $f_4 = 2397.5$  MHz; RF performance at  $V_{DS} = 28$  V;  $I_{Dq} = 900$  mA;  $T_{case} = 25$  °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	$P_{L(AV)} = 25 \text{ W}$	<tbd></tbd>	17	-	dB
$\eta_D$	drain efficiency	$P_{L(AV)} = 25 W$	<tbd></tbd>	28	-	%
RL <sub>in</sub>	input return loss	$P_{L(AV)} = 25 W$	-	-10	-	dB
$ACPR_{5M}$	adjacent channel power ratio (5 MHz)	$P_{L(AV)} = 25 W$	-	-32	<tbd></tbd>	dBc

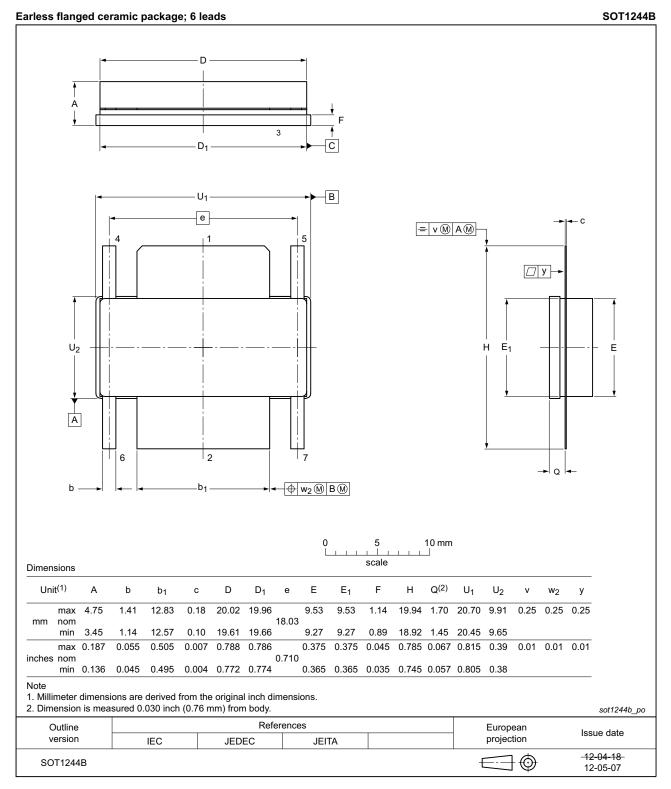
### 7. Test information

#### 7.1 Ruggedness in class-AB operation

The BLF8G24LS-100V and BLF8G24LS-100GV are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS} = 28$  V;  $I_{Dq} = 900$  mA;  $P_L = 100$  W; f = 2300 MHz.

**Power LDMOS transistor** 

### 8. Package outline



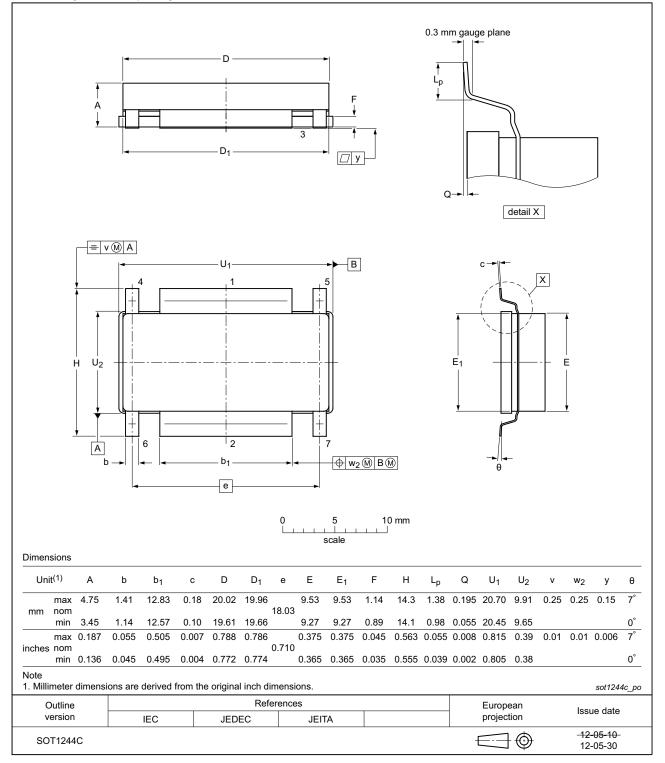
#### Fig 1. Package outline SOT1244B

BLF8G24LS-100V\_24LS-100GV

**Objective data sheet** 

SOT1244C

Earless flanged ceramic package; 6 leads



#### Fig 2. Package outline SOT1244C

### 9. Handling information

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

### **10. Abbreviations**

Table 8.	Abbreviations
Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
PAR	Peak-to-Average Ratio
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

### **11. Revision history**

Table 9.	Revision history				
Documen	t ID	Release date	Data sheet status	Change notice	Supersedes
BLF8G24LS-100V_24LS-100GV v.1		20131104	Objective data sheet	-	-

### 12. Legal information

#### 12.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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## **BLF8G24LS-100(G)V**

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